

III. Please replace the original ABSTRACT, Page 9, with the following amended ABSTRACT:

ABSTRACT OF THE DISCLOSURE

~~With oxygen retaining protectors for copper interconnects grown by sheet-to-sheet displacement deposition to remove the oxygen in the reaction solution before deposition of copper film onto the wire such that the copper film contacting wire is grown at a lower electrical resistance.~~

A solvent such as deionized water is heated up to boil to remove the oxygen dissolved in the water before preparing the plating solutions for the growth of copper interconnects. The resistance of the copper grown from the EDD solutions having undergone the oxygen-removing process is greatly improved, down to a value very close to copper's ideal value.